

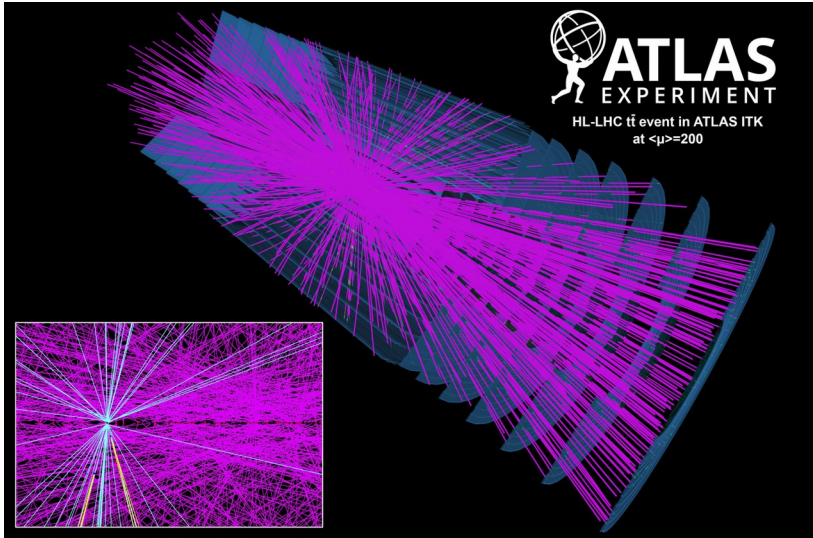
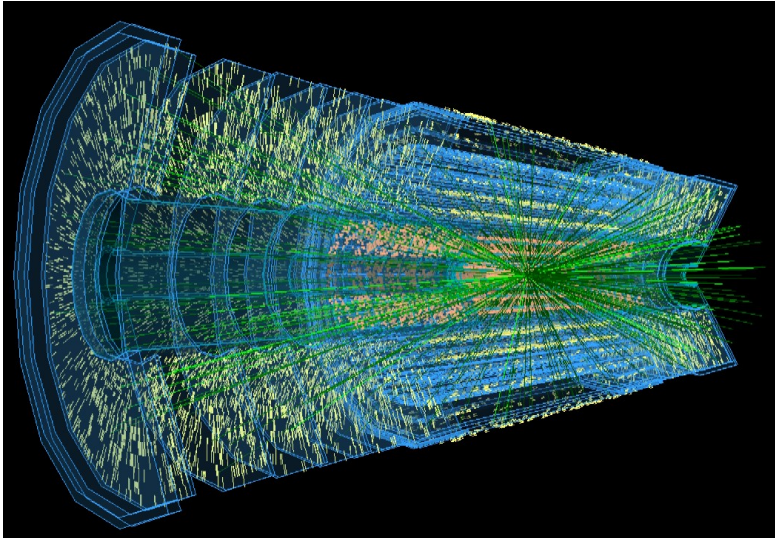
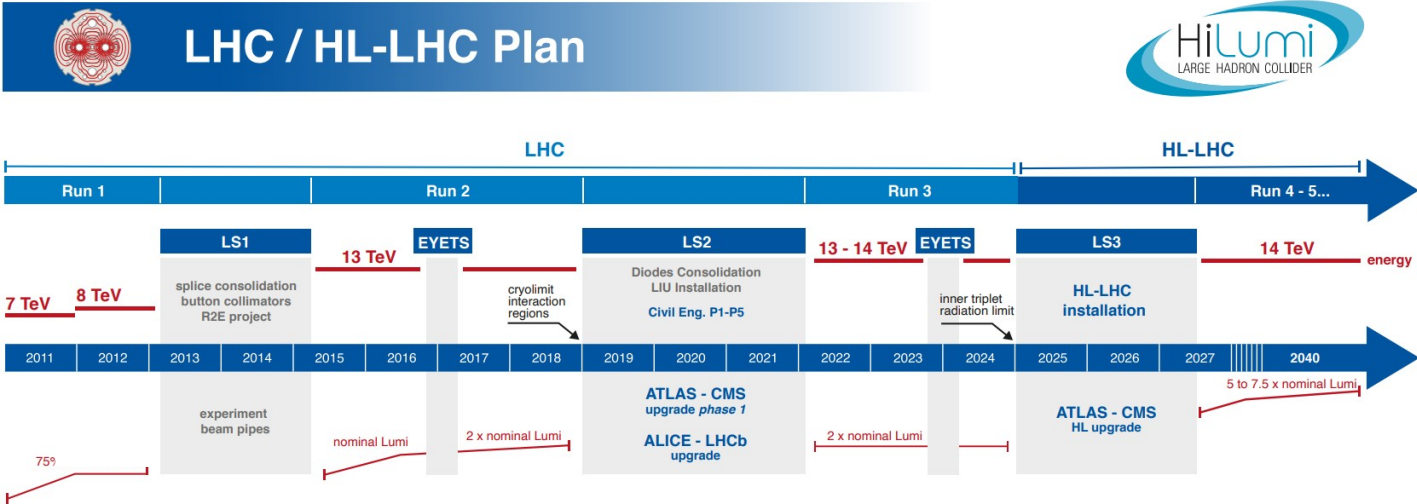
# Tower Jazz 180 nm MALTA monolithic active pixel sensor Test Beam results

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# Future-proofing design

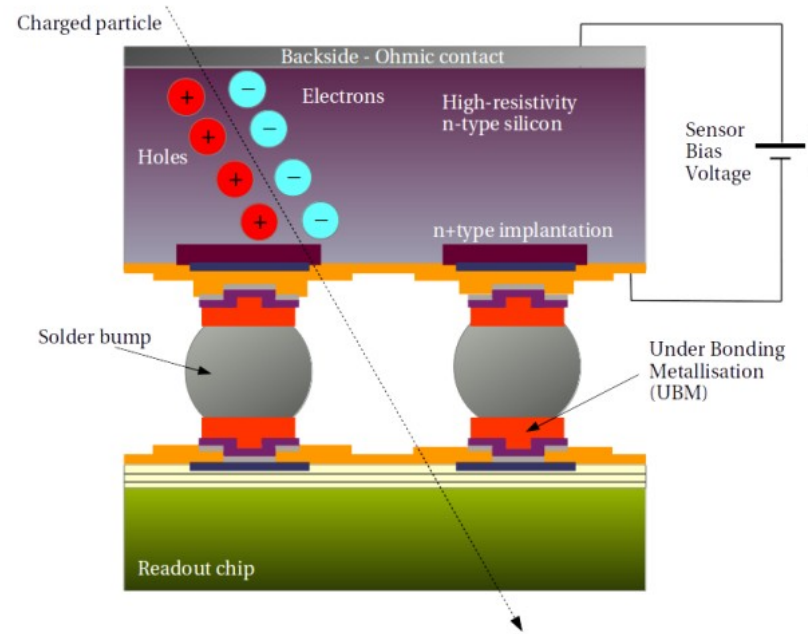
- Very high radiation tolerance (1 – 2E15 neq/cm<sup>2</sup>; 80 Mrad TID)
- High granularity (2MHz/mm<sup>2</sup> hit rates)
- Good timing response (<25 ns)
- Low material budget (cooling, power consumption)
- Large surface area
- Very thin



# MAPS

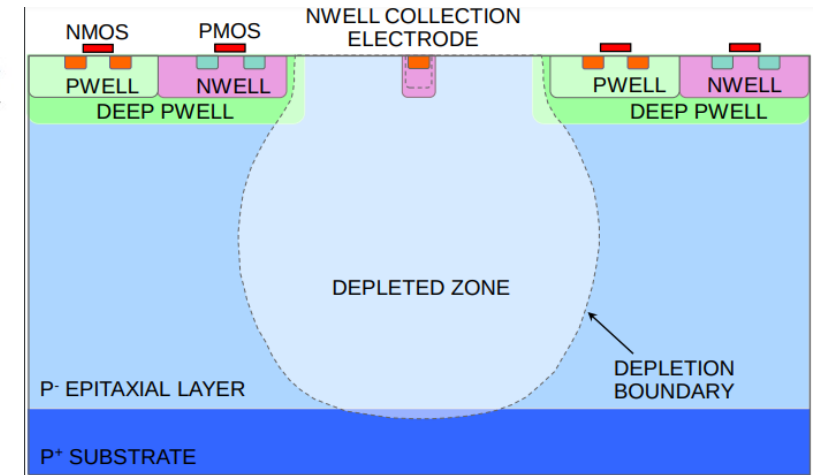
## Monolithic Active Pixel Sensors advantages:

- **Integration** of RO electronics and sensor in one die
- **Smaller pixel pitch**
- **Small sensor capacitance** (< 5 fF)
  - higher voltage signal
  - better power/performance
  - reduced material budget for powering and cooling



### Hybrid sensors

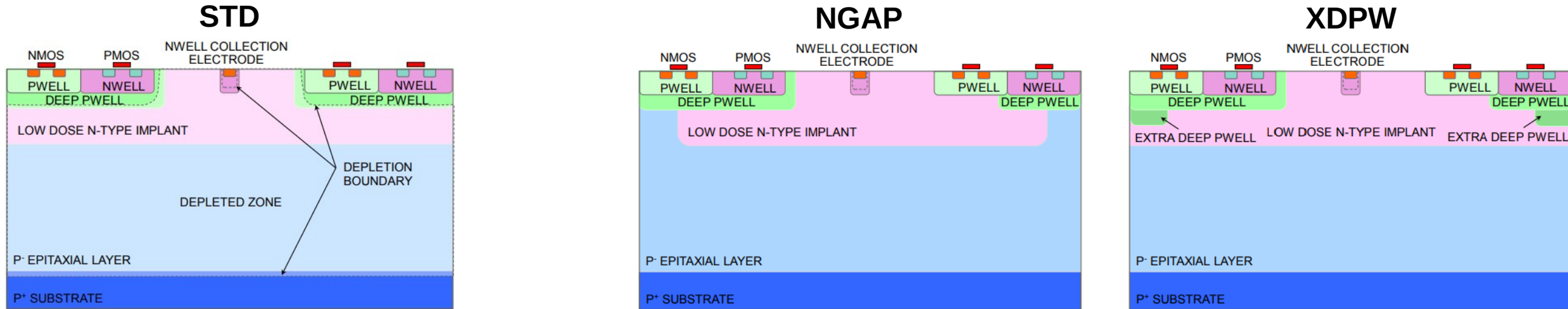
- Two chips (sensor, ROC)
- Large electrodes, capacitance
- Expensive bump bonding
- Well understood radiation hardness



### Monolithic sensors

- One chip = (Sensor + ROC)
- Smaller electrodes, capacitance
- Less material; lower power needs
- Radiation effects still being studied

# TJ 180nm CMOS MALTA Process

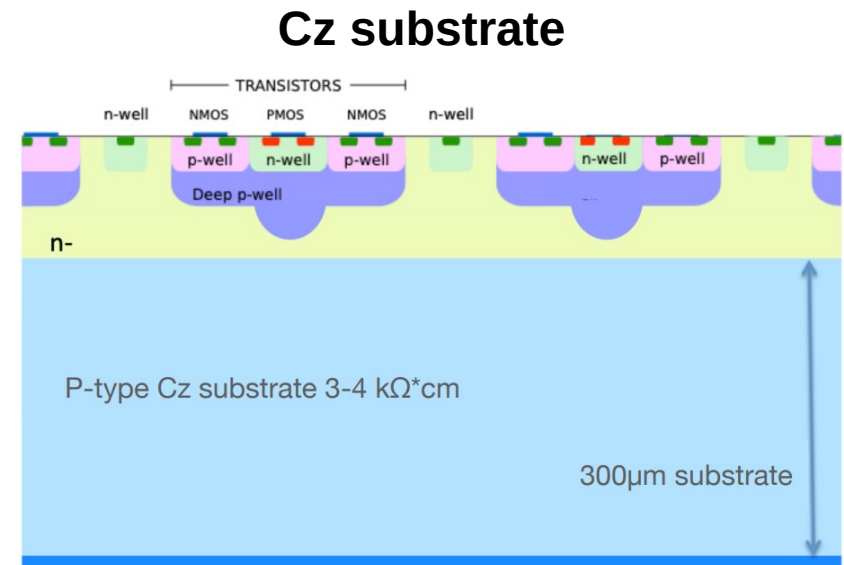


## 3 CMOS flavours:

- **STD** Extra N-type implant for improved depletion zone
- **NGAP** Gap in the low dose N-type implant
- **XDPW** Extra Deep P-Well

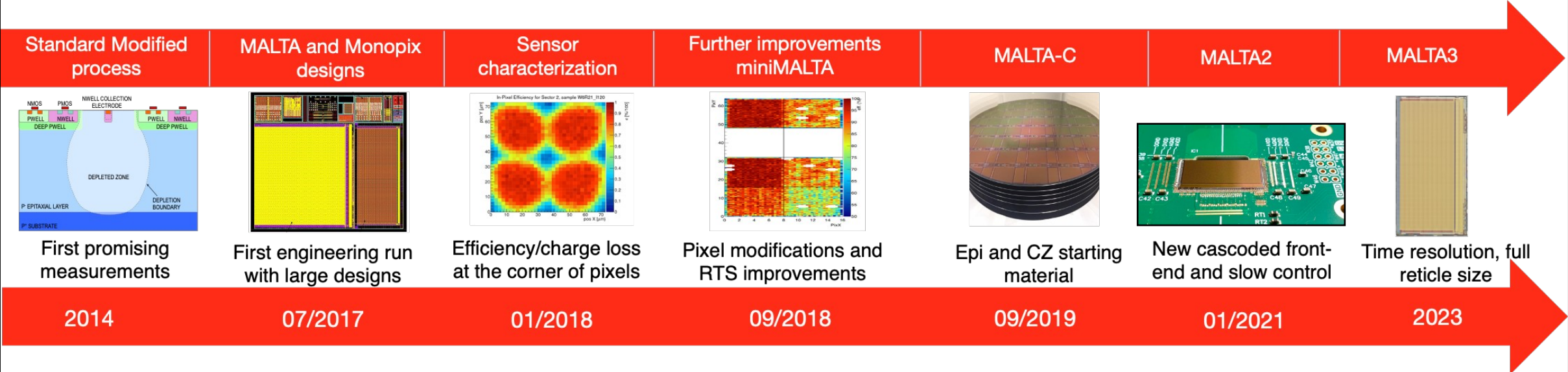
## 2 different substrates:

- High Resistivity Epitaxial layer (**Epi**)
- Czochralski (**Cz**)





# R&D MALTA Timeline



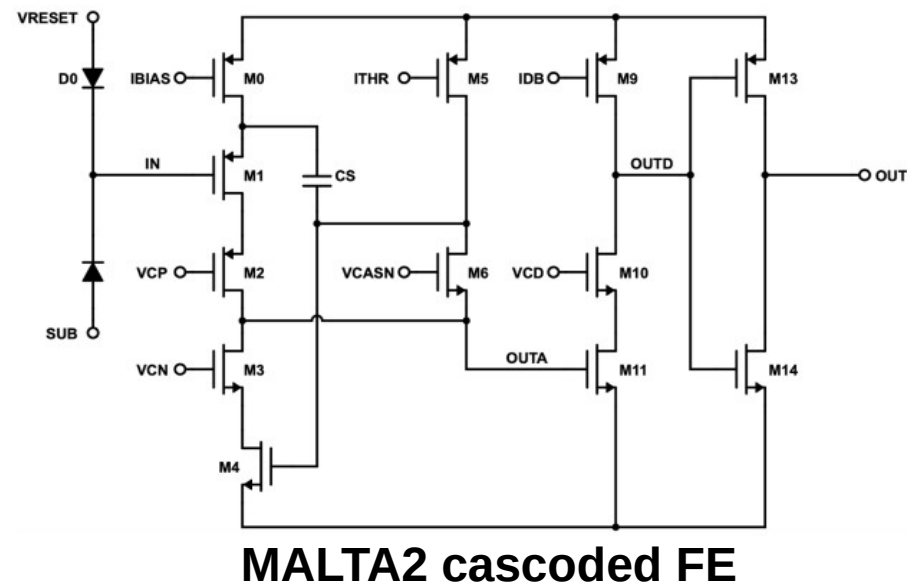
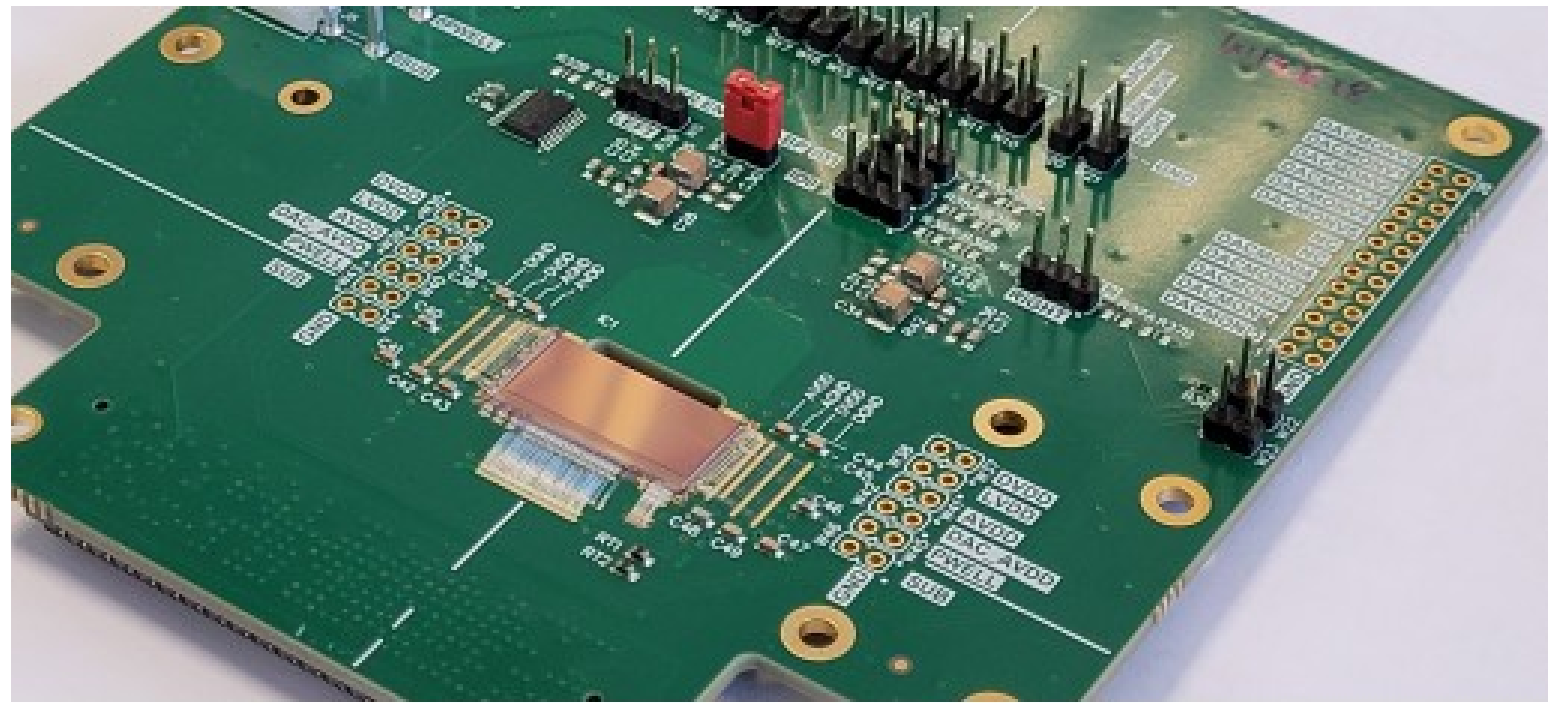
- ### MALTA
- First large demonstrator (**2x2 cm<sup>2</sup>**)
  - 8 sectors with different pixel flavors
  - **Asynchronous readout**
  - Sensor functional. Slow control issues

- ### miniMALTA
- Small demonstrator (**1.7x0.5 mm<sup>2</sup>**)
  - Serial output
  - **Cascoded FE**
  - Rad hard, RTS improvements

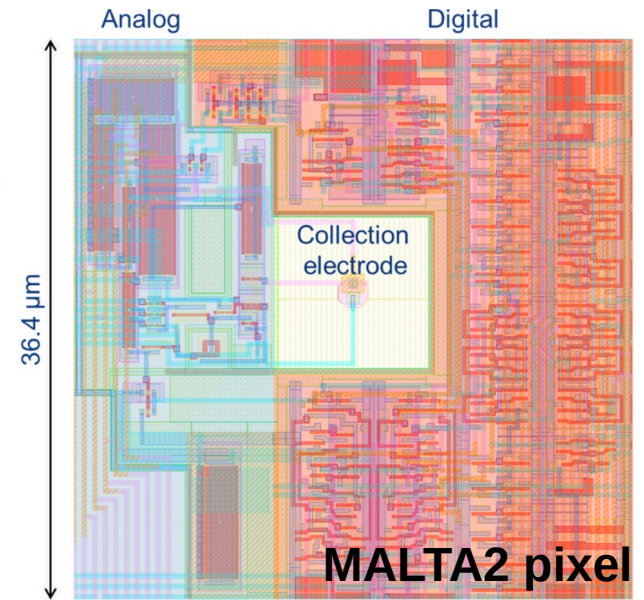
- ### MALTA2
- Smaller matrix (**2x1 cm<sup>2</sup>**)
  - **New Slow control**
  - Mini-MALTA FE
  - Under test!

# TowerJazz MALTA2

- 224 x 512 pixels (36.4  $\mu\text{m}$  pitch)
- **Small** collection electrode (2-3  $\mu\text{m}^2$ )
- **Low** power consumption:
  - 1  $\mu\text{W}$ /pixel analog power
  - 70  $\text{mW}/\text{cm}^2$  analog power
  - 10  $\text{mW}/\text{cm}^2$  digital power
- **Asynchronous readout**  
(No distributed clock across matrix)
- New **cascoded** FE (M3) & **enlarged** M4



MALTA2 cascoded FE

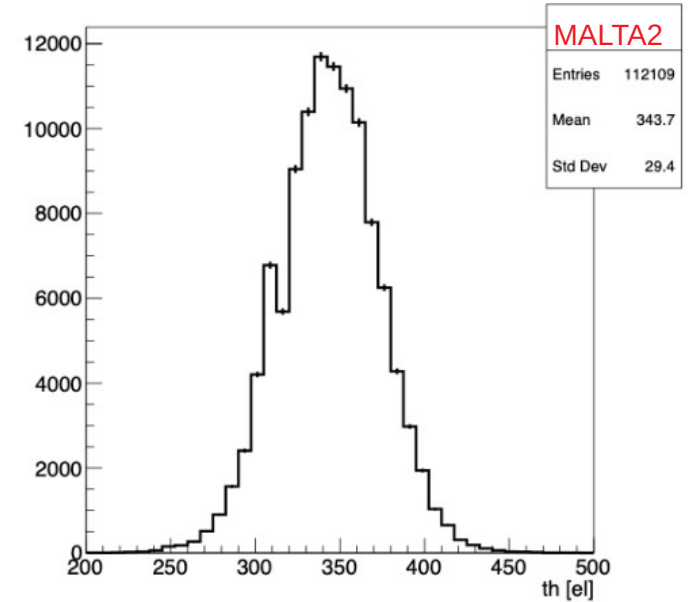
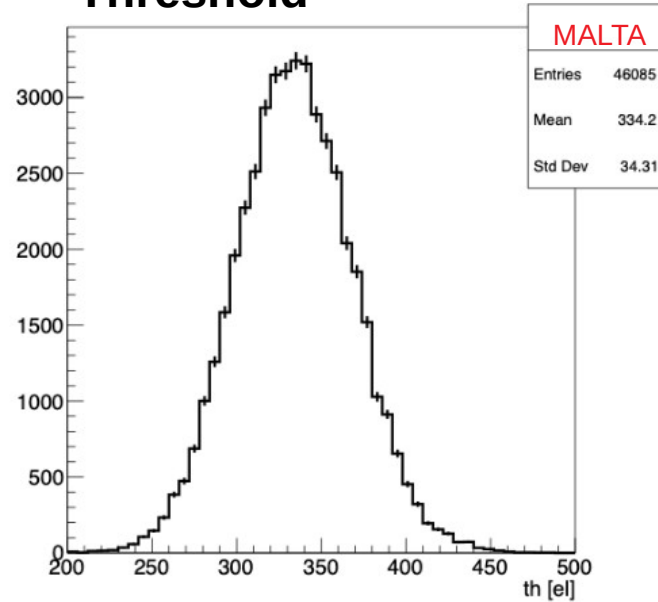


MALTA2 pixel

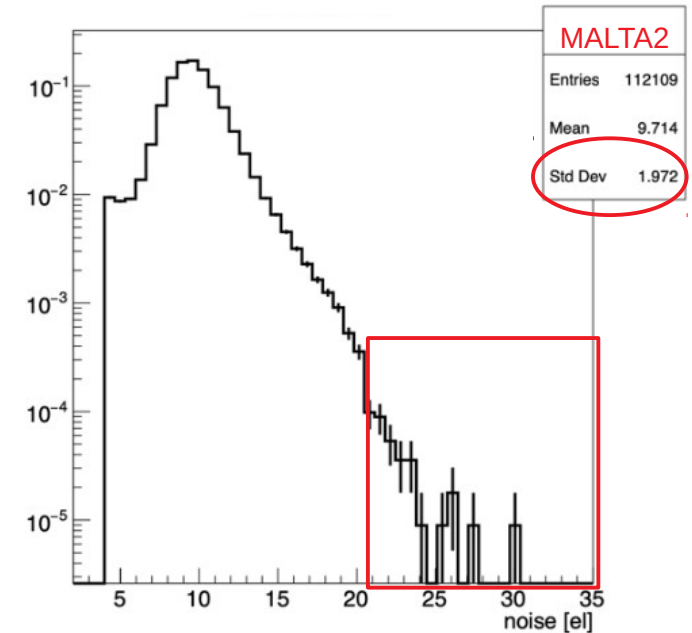
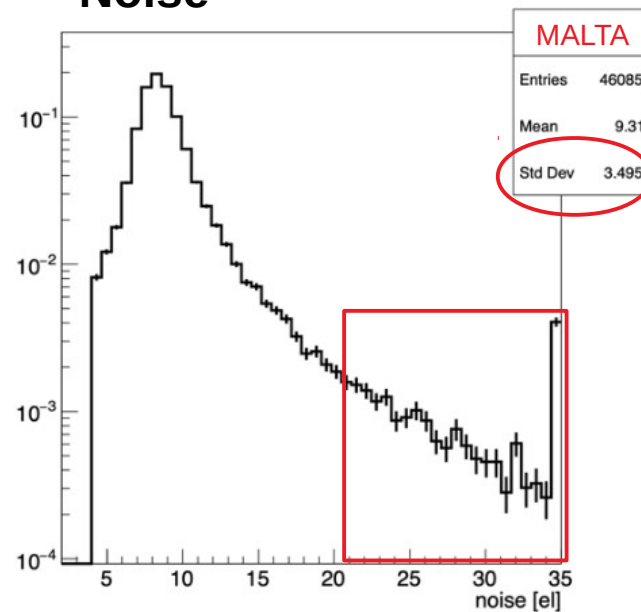
# Threshold & noise

- **Threshold & noise** scans for MALTA, MALTA2 (Epi, NGAP, high doping of the n-blanket at -6V substrate voltage)
- **Similar threshold dispersion (10%)** around 340 electrons for both MALTA & MALTA2
- MALTA2 (cascoded FE) has **much lower non-gaussian tail (RTS)**, compared to MALTA

## Threshold



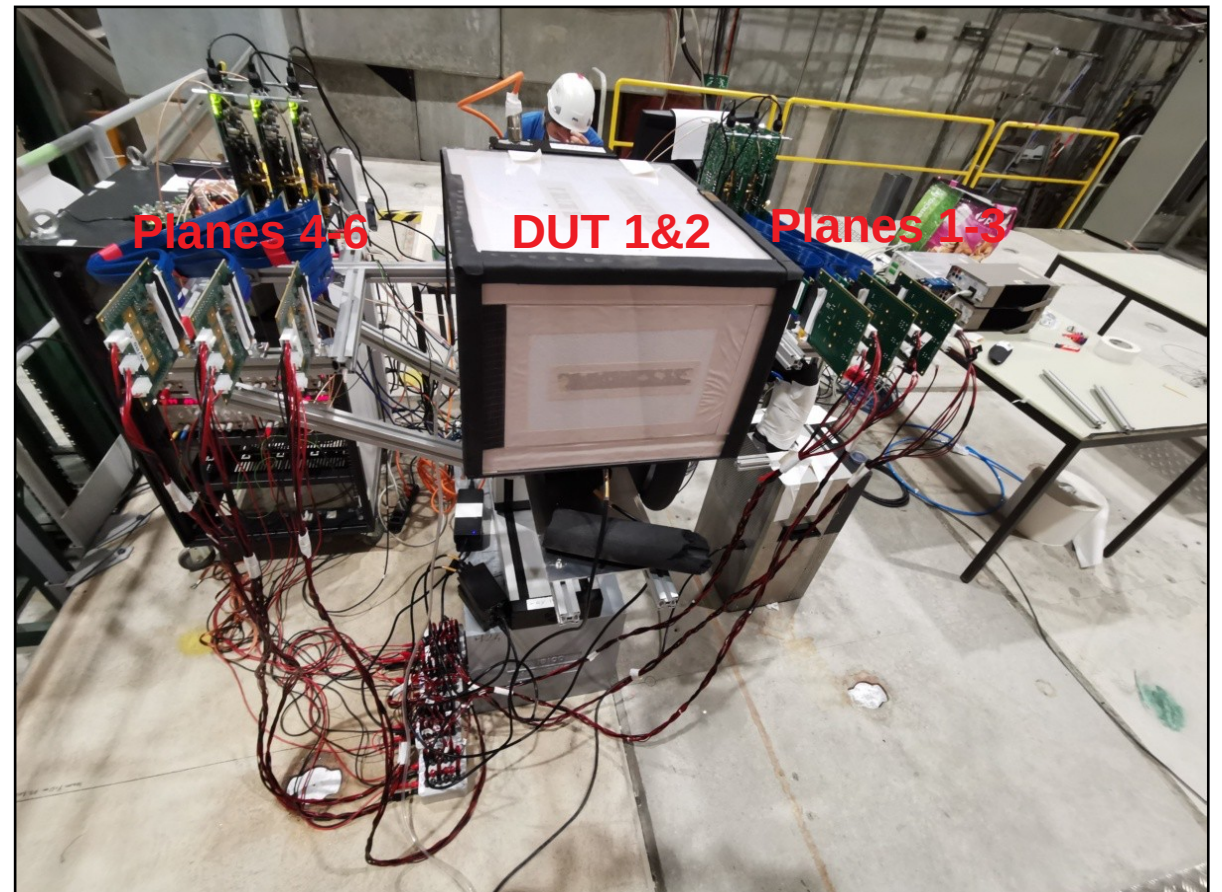
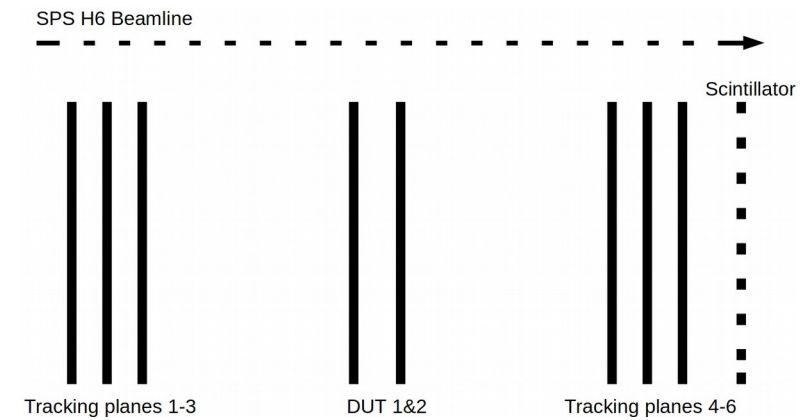
## Noise





# MALTA SPS Telescope

- **Malta Telescope** operated the whole of 2021 at CERN SPS H6 beamline. Aiming for the same for 2022!
- **2021 SPS Test beam** Testing of MALTA2:
  - MALTA 2 performance
  - Radiation tolerance
  - Timing performance
- **Six MALTA tracking planes** (2x Cz, 4 Epi), Scintillator and Cold Box with capacity for up to 2 DUTs



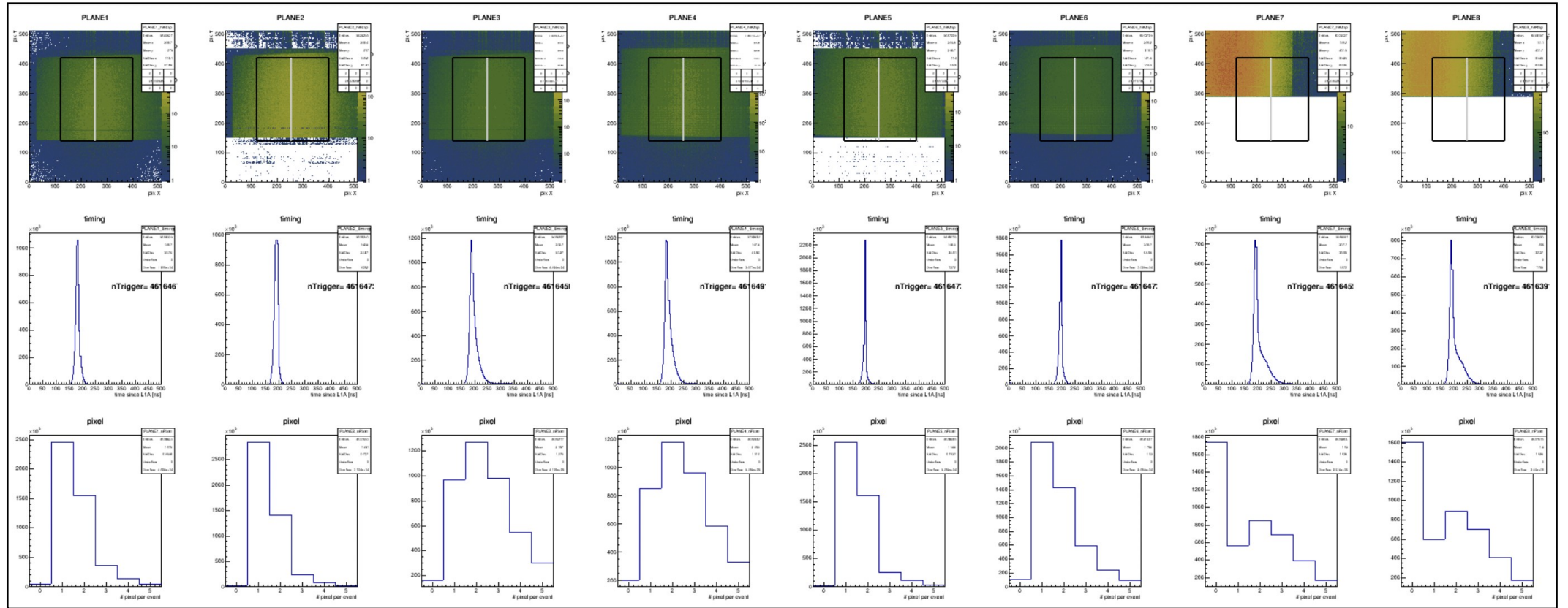


# SPS Testbeam Monitoring plots

Hitmap

Time since L1A

#pixel/  
event



- DAQ with **online monitoring** (hit map, time distribution, number of hits per-event)
- **Fast track reconstruction** due to low noise/ occupancy (~1.2 hits/plane/event)

# MALTA2 Timing

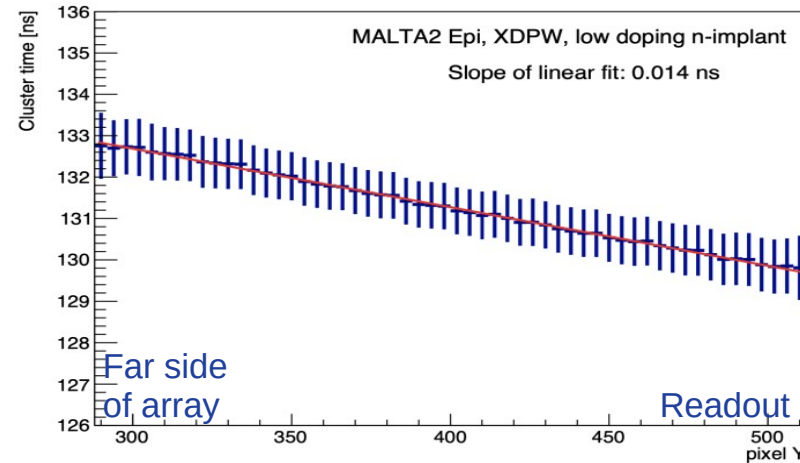
Time of arrival of the fastest hit in a matched cluster w.r.t scintillator reference, as a function of the matrix X/Y coordinate

- **Timing corrections:**

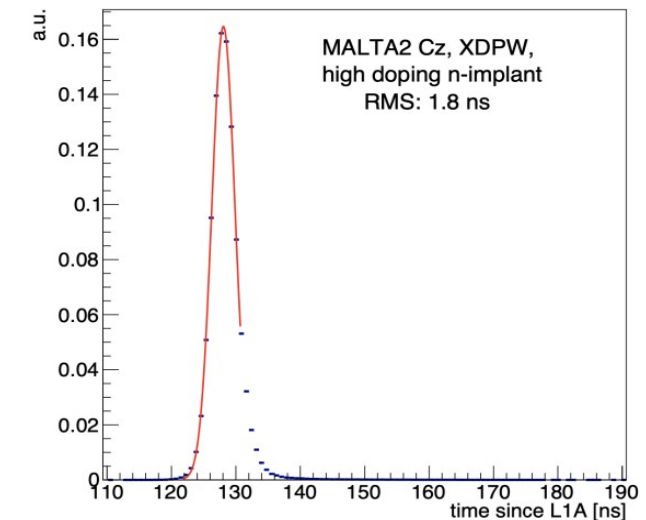
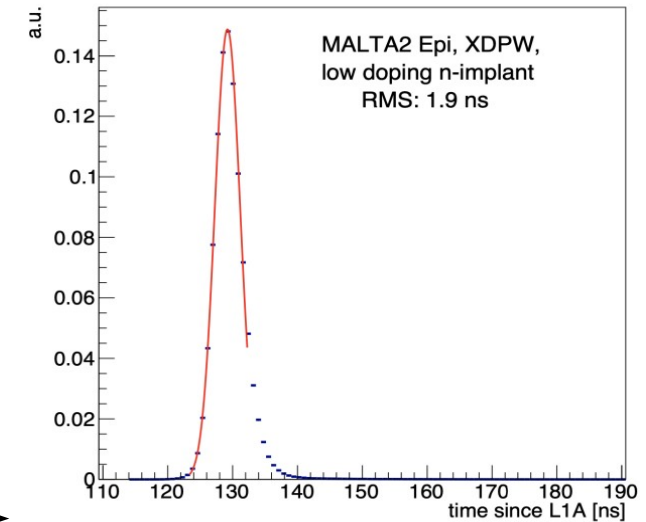
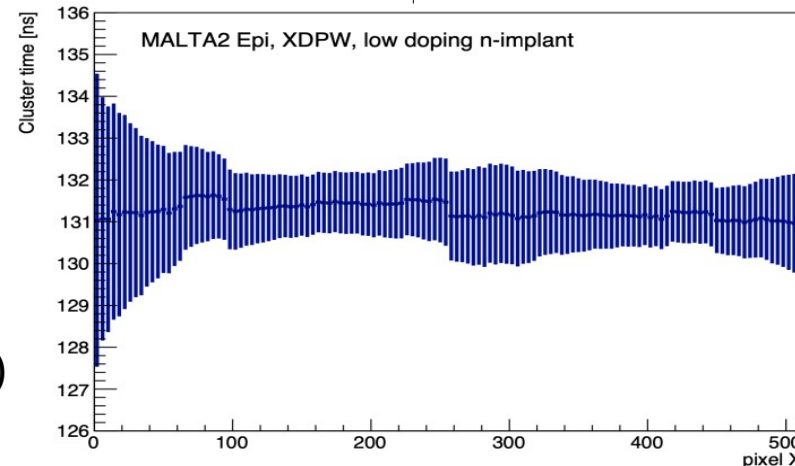
- **(Y)** Linear due to column time propagation (**top**)
- **(X)** Non-uniform chip response in the row direction (**bottom**)

- The **timing plots** are a convolution of:

- Electronics jitter
- Time-walk
- Charge collection effects
- Scintillator jitter (500ps)
- FPGA readout jitter (900ps)

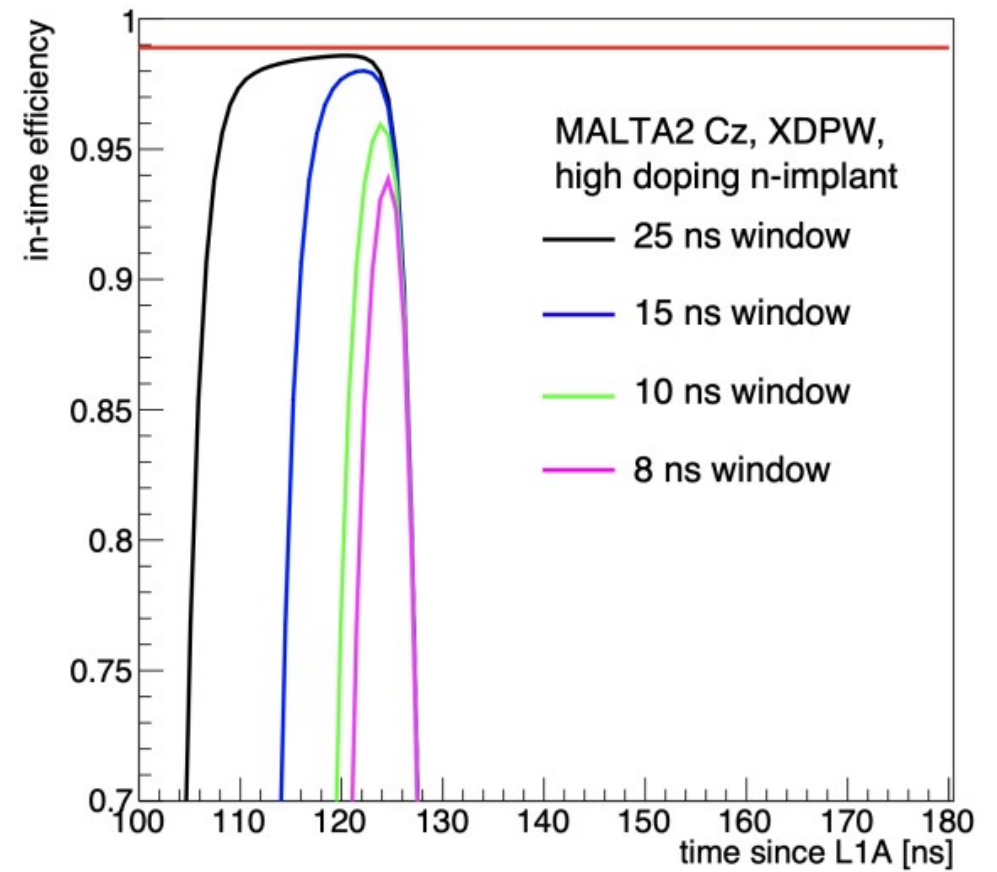
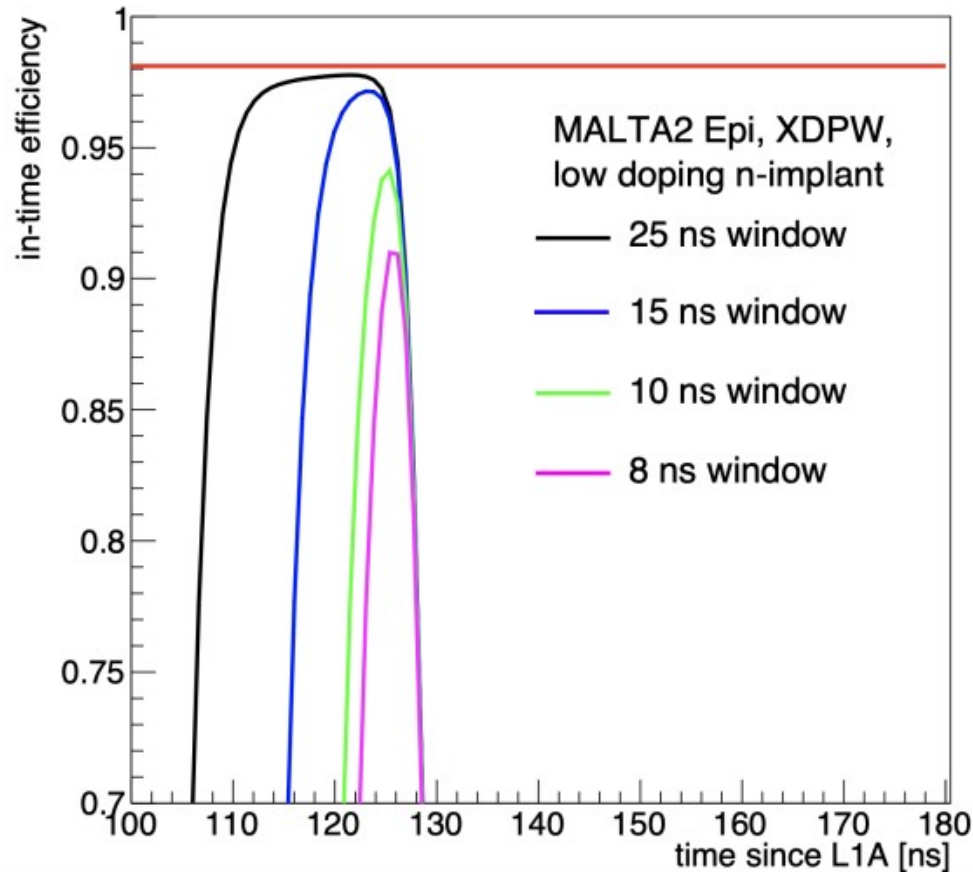


Apply corrections



# MALTA2 Timing

In-time efficiency for a sliding window of 25,15,10,8 ns w.r.t a scintillator

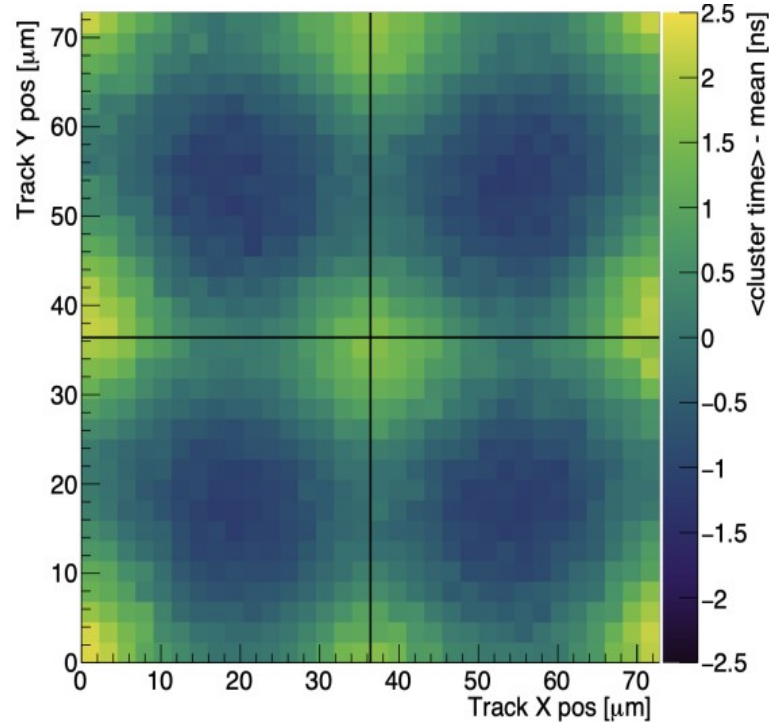


- **LHC 25 ns** bunch spacing: **>98%** of MALTA2 signals arrive; **FCC-ee <15 ns** bunch spacing: **>95%** of MALTA2 signal arrive; **> 90%** in-time efficiency for **8 ns window**
- **Cz** has **5% better** collection for a 8 ns window

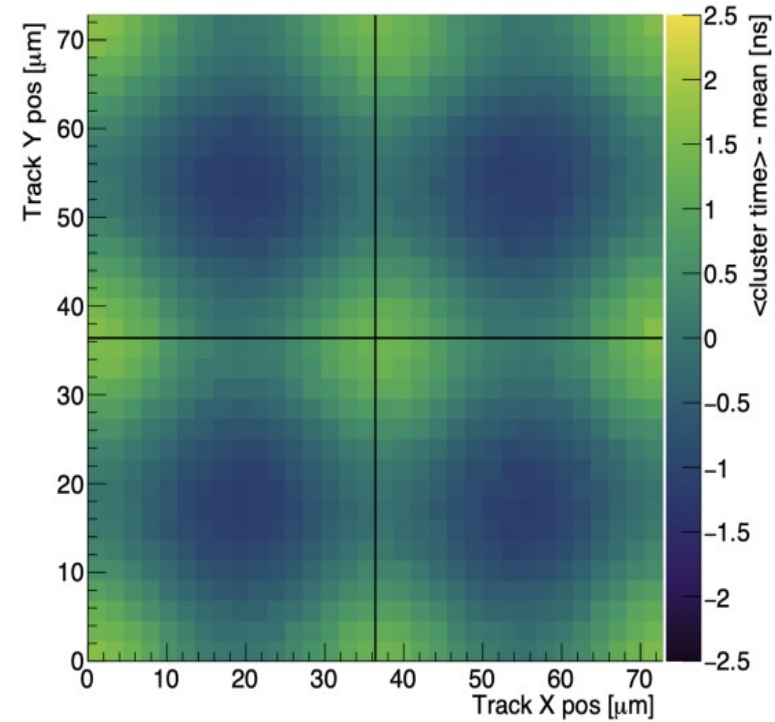
# MALTA2 Timing

In pixel cluster timing, projected over 2x2 pixel matrix for a Cz and for an Epi MALTA2 sample (XDPW, 100 micron, low doping of the n-implant)

MALTA2 Cz. XDPW 100 $\mu$ m, low doping of n-implant



MALTA2 Epi. XDPW 100 $\mu$ m, low doping of n-implant



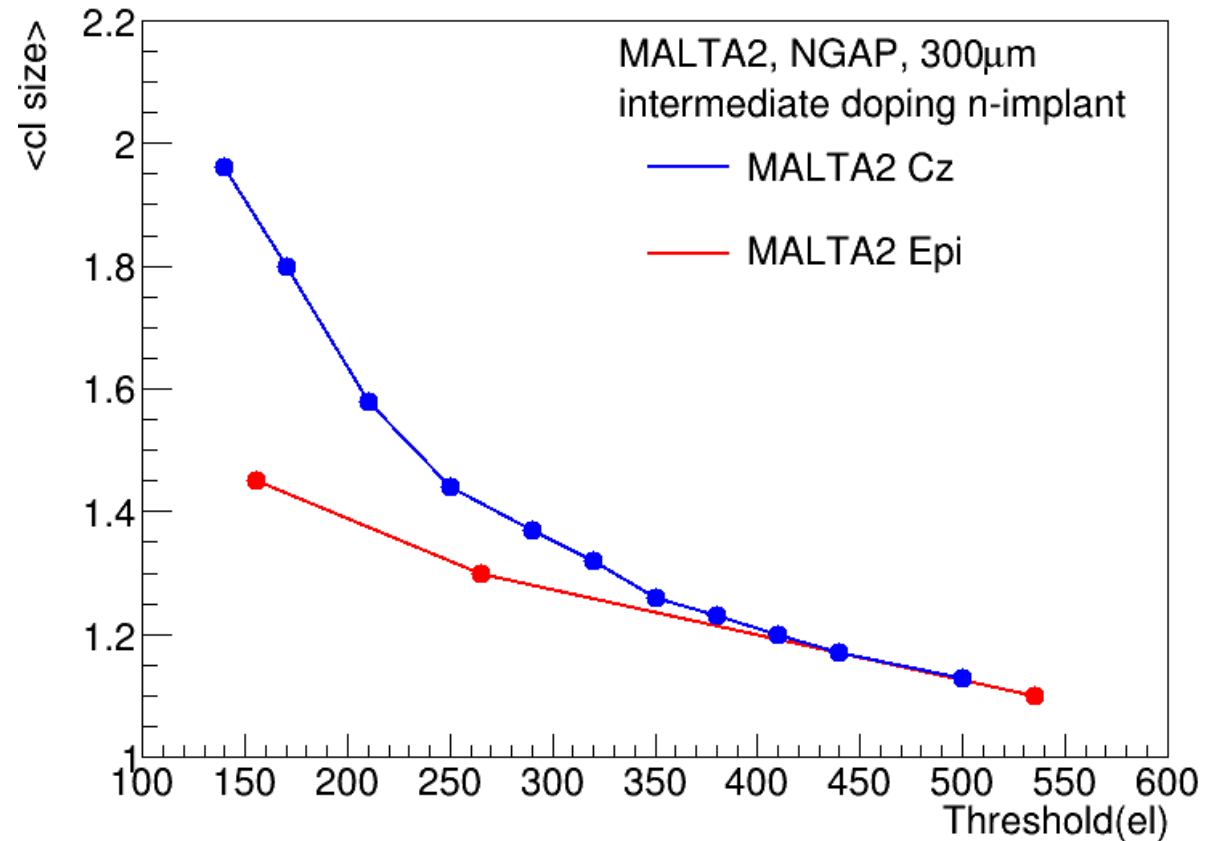
Threshold: 170  $e^-$  @ -6V SUB voltage

- Pixel corners generate late-arriving signals
- Non-irradiated **Cz** and **Epi** sample have **similar** in pixel cluster timing



# Cz vs EPI

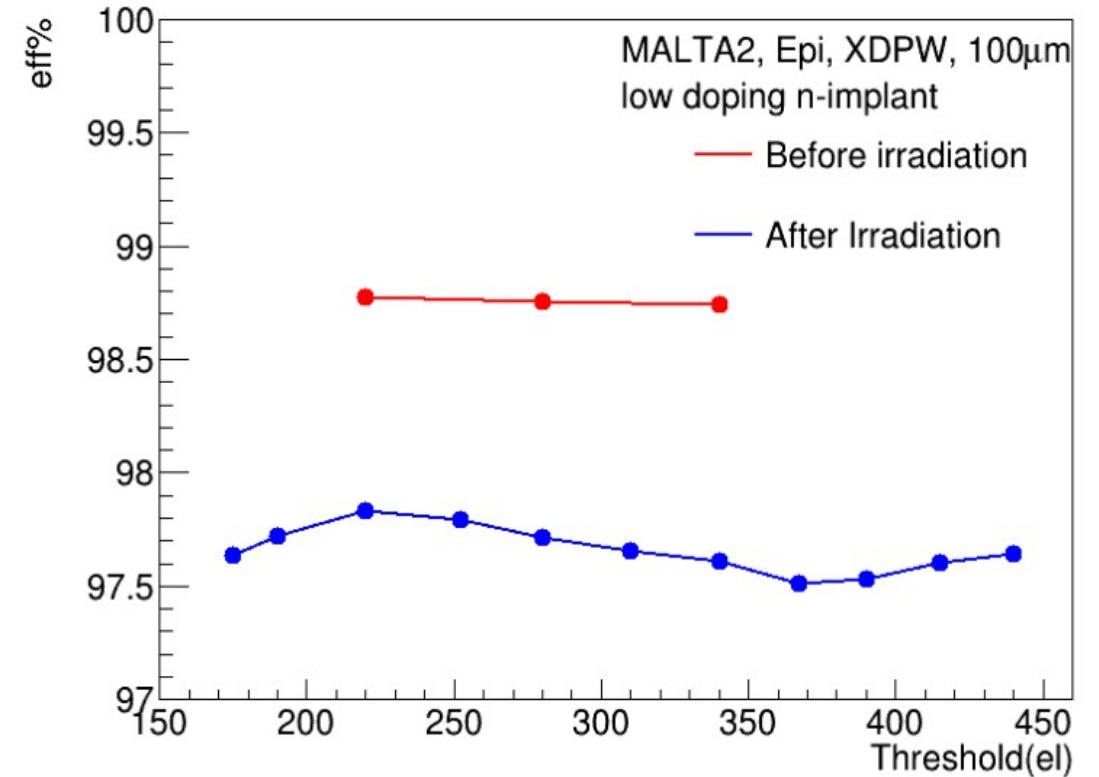
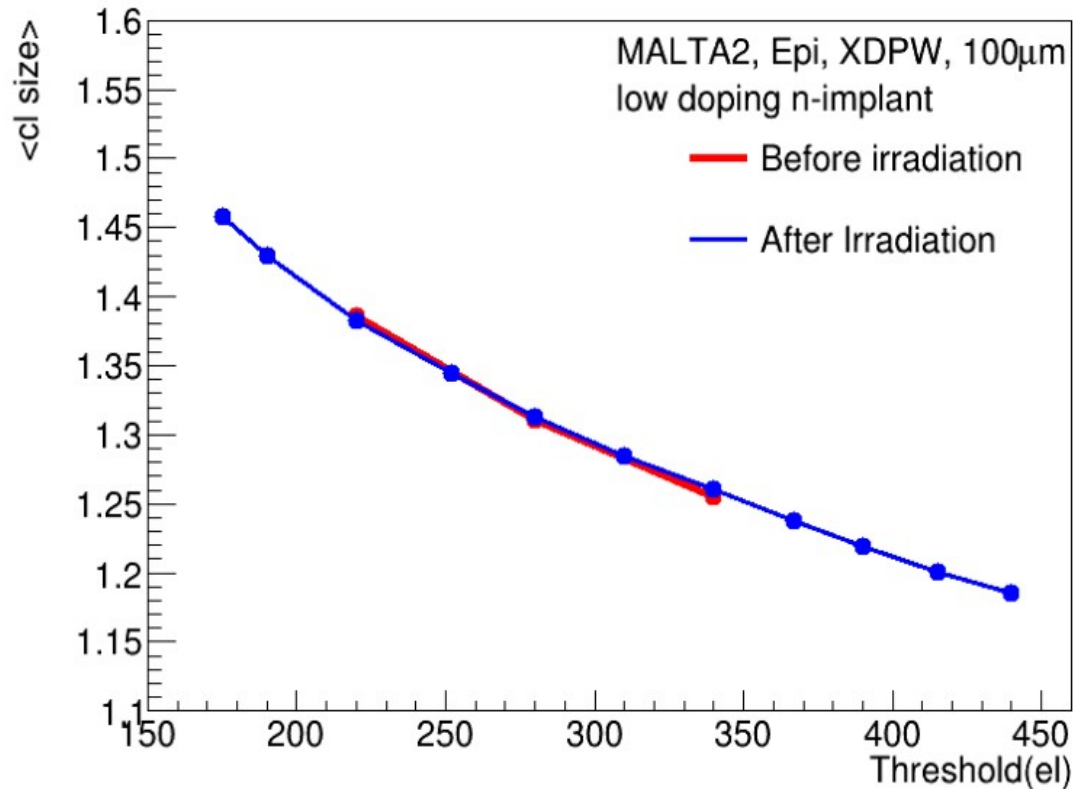
Average cluster size vs threshold in electrons for a MALTA2 Epi and a MALTA2 Cz sample



- **Strong dependence** of cluster size on threshold for both Epi and Cz samples at -6V substrate voltage
- Larger depletion voltage & signal of the high resistivity Cz substrate → **higher cl size at lower thresholds**

# 100 Mrad xray

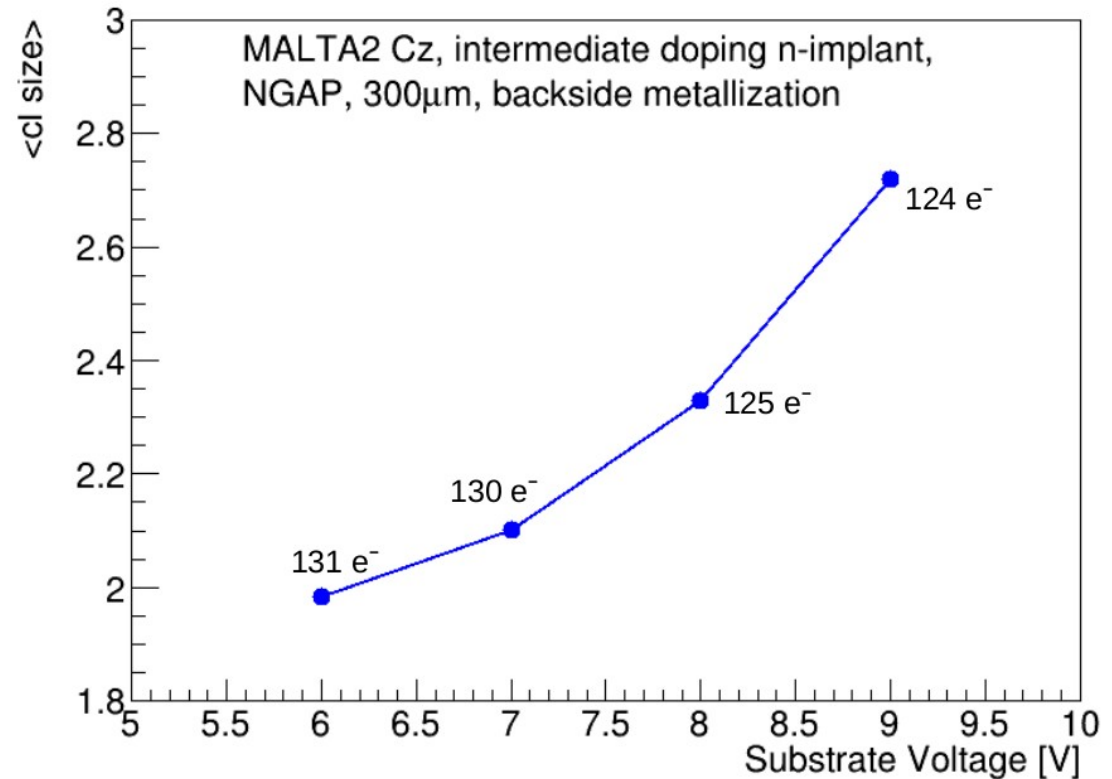
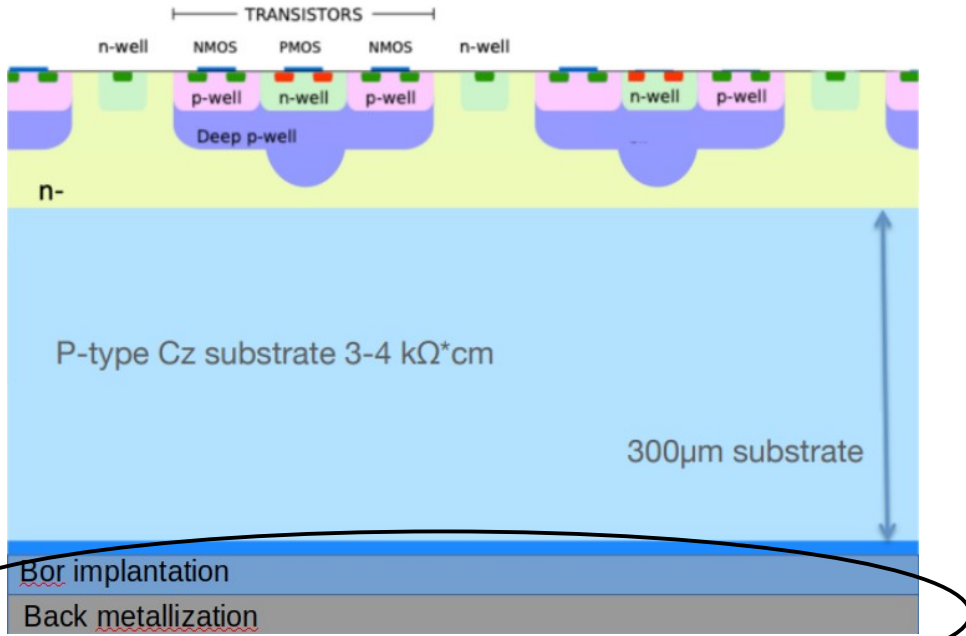
Average cl size (left) and efficiency (right) in terms of threshold in electrons before and after 100 Mrad Xray irradiation of the same MALTA2 Epi



- **Strong dependence of cluster size** on threshold; relatively **flat dependence of efficiency** on threshold for -6V substrate voltage
- **After 100 Mrad Xray, MALTA2 performance is similar:** cluster size and efficiency (>97%) **within 2%**

# Backside metallization

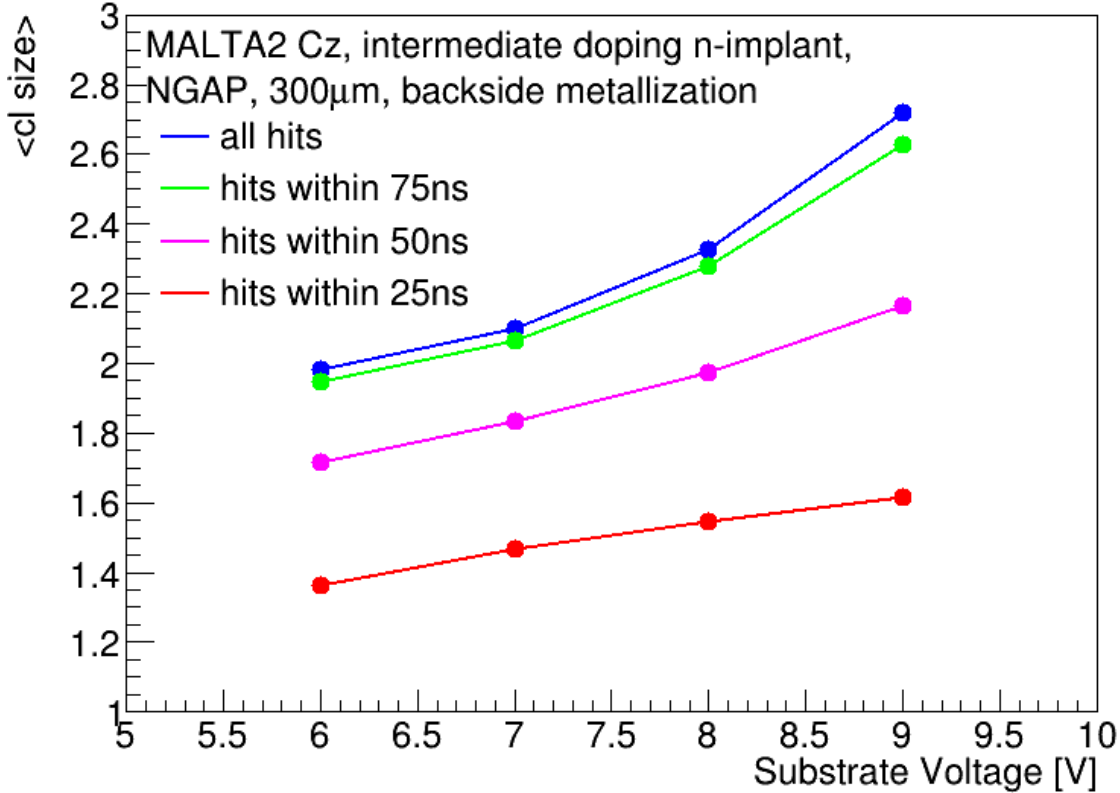
Average cluster size vs SUB voltage of a MALTA2 Cz, back metallized



- No P+ substrate → non-homogeneous depletion regions. Back metallization leads to **better propagation of the substrate voltage** → homogeneous electric field
- Very strong increase in cluster size with SUB voltage. A cl size of **2.7±0.1** was achieved for -9V SUB voltage

# Backside metallization

The cluster size is computed only for hits arriving in a time window (75,50,25 ns) relative to the median hit arrival time



- **Full cluster** collection needs **3 bunch crossings** (75ns). (for ITK outerlayer occupancy - acceptable)
- To be improved with **MALTA3**



# Conclusion and outlook

- Significant improvements in terms of noise for MALTA2, due to its cascoded FE and also improved slow control and radiation hardness.
- SPS 2021 Measurement Campaign:
  - MALTA 2 performance
  - Radiation tolerance
  - Timing performance
- Further analysis is planned on neutron and proton irradiated MALTA 2 samples during the 2022 SPS Testbeam!
- MALTA3 expected for 2023!

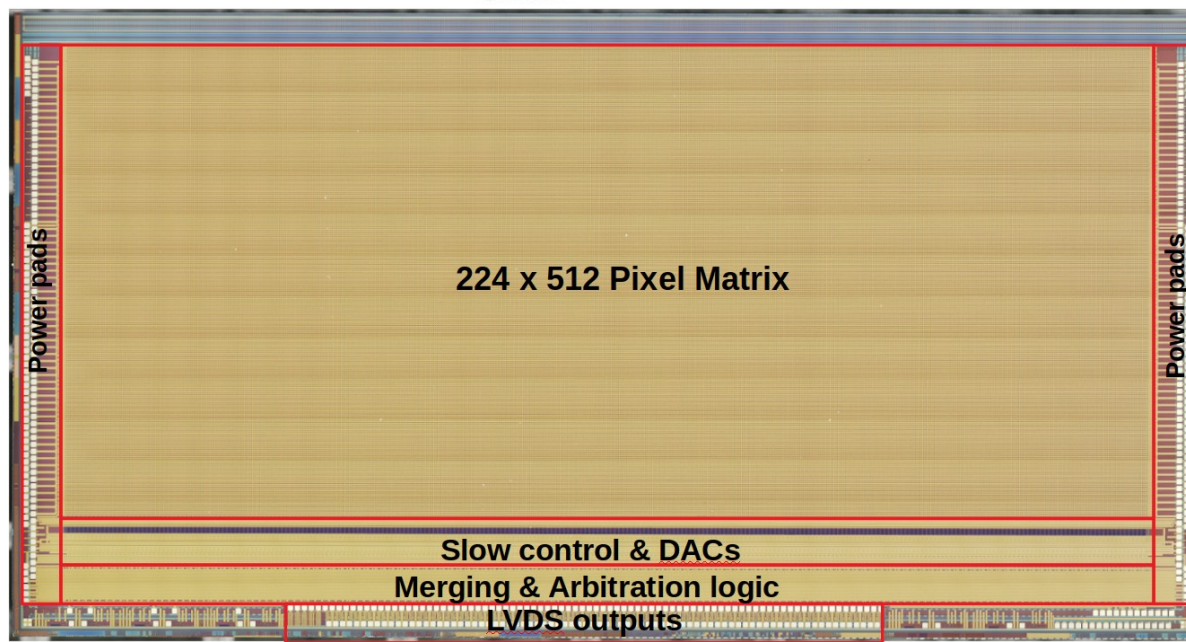
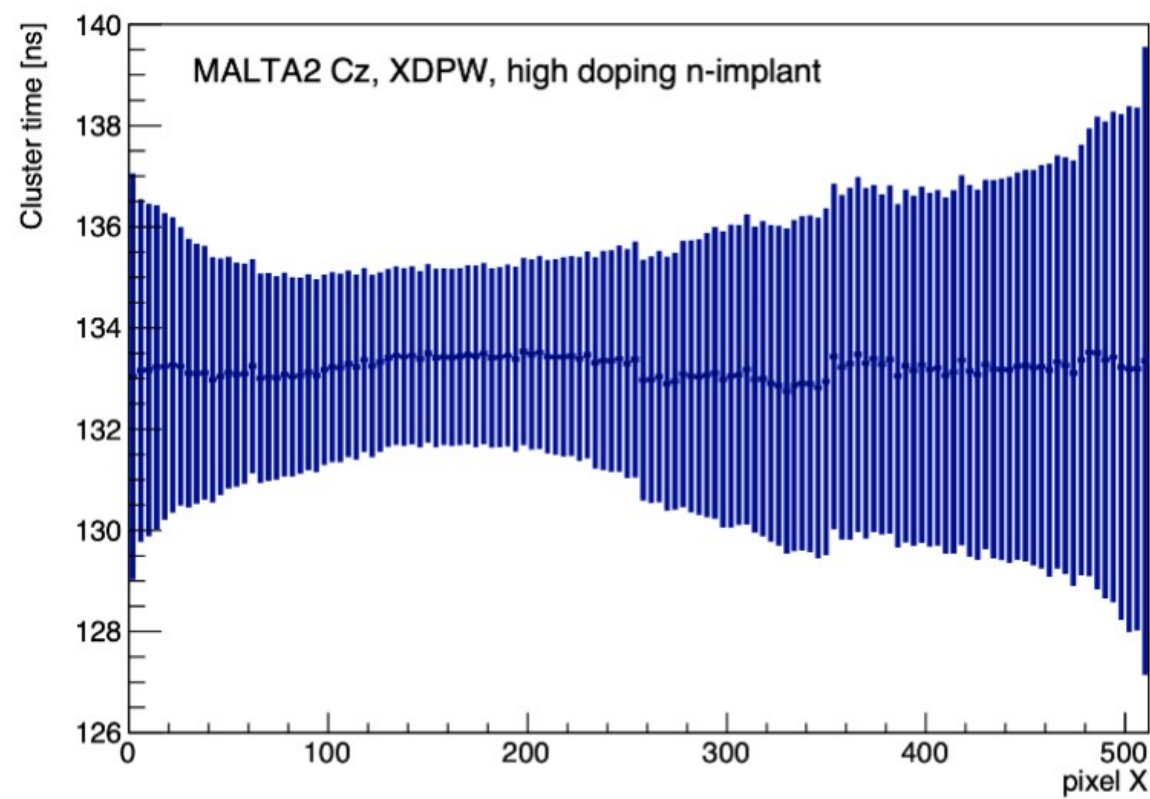
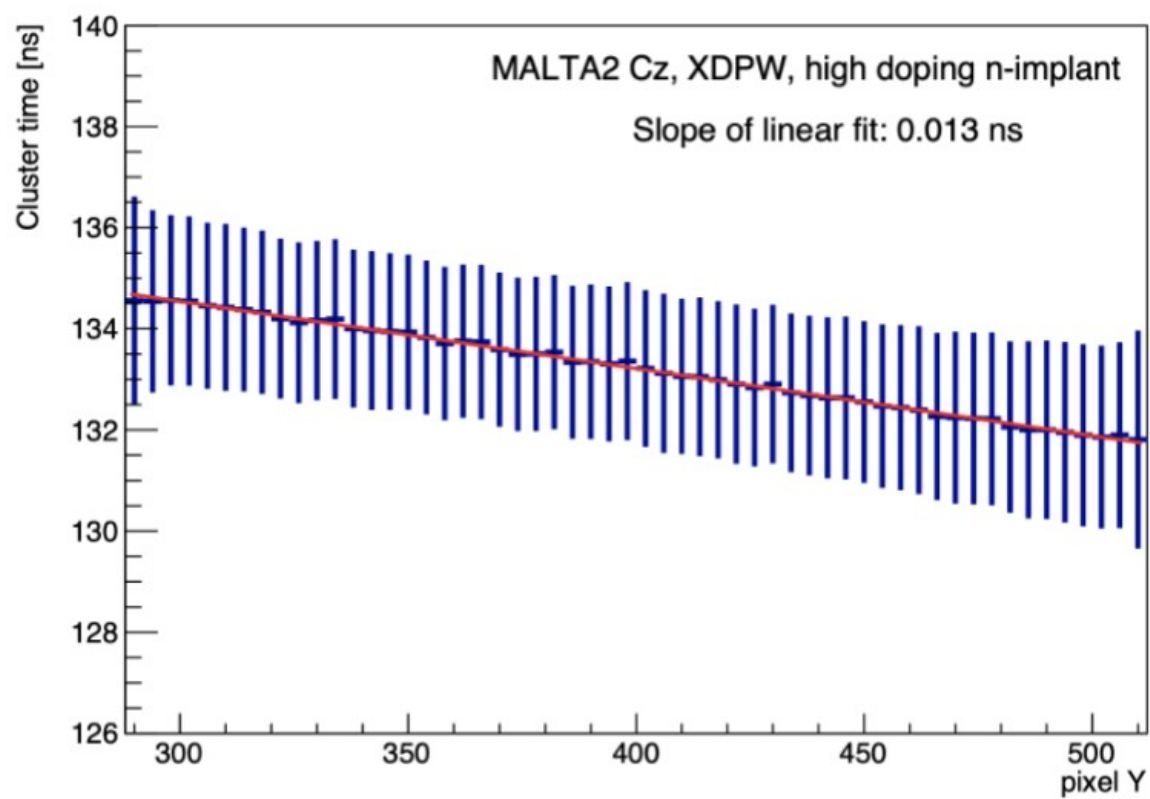
# Acknowledgments

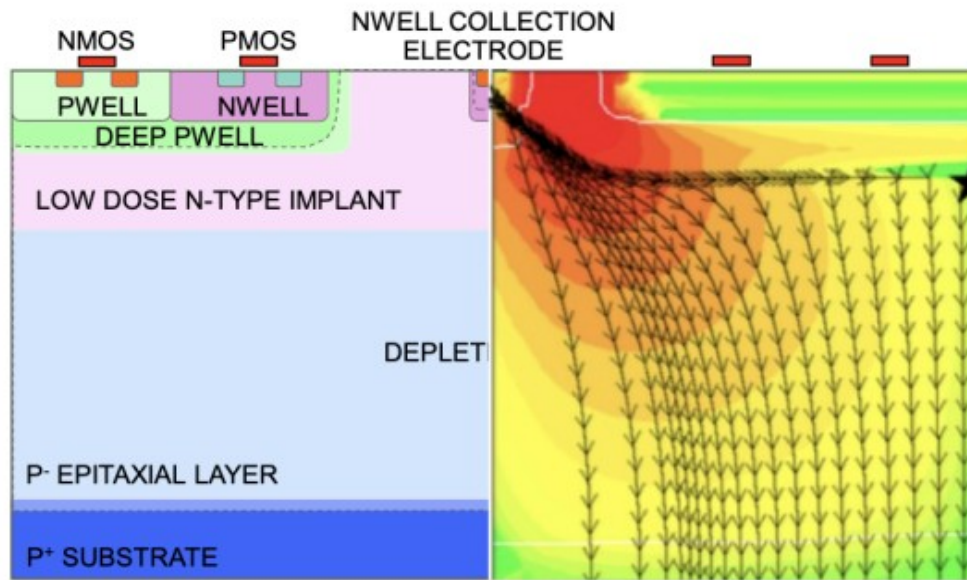
- This project has received funding from the European Union's Horizon 2020 Research and Innovation programme under grant agreement No 101004761.
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**Thank you**

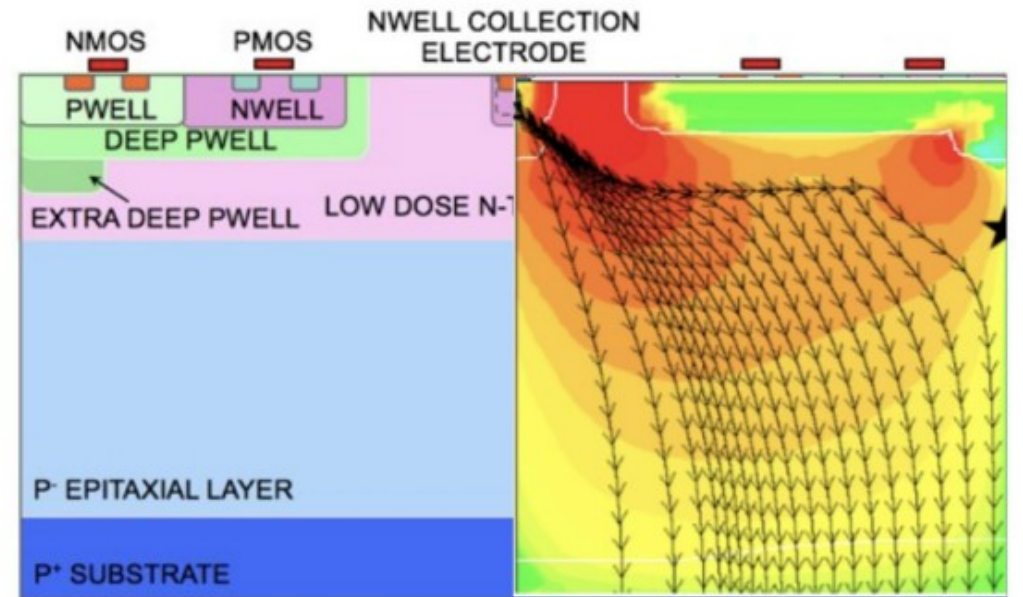
# Bonus



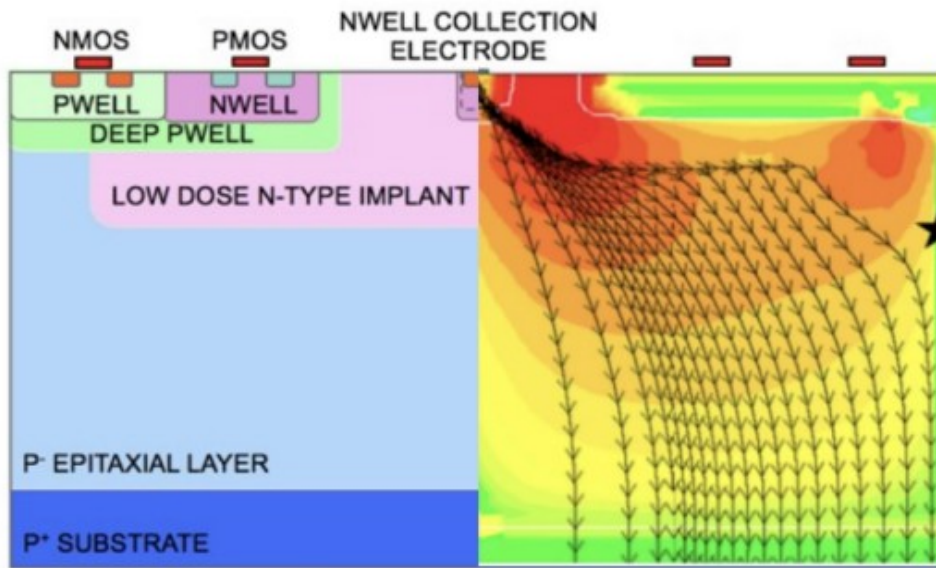




**Standard modified process**

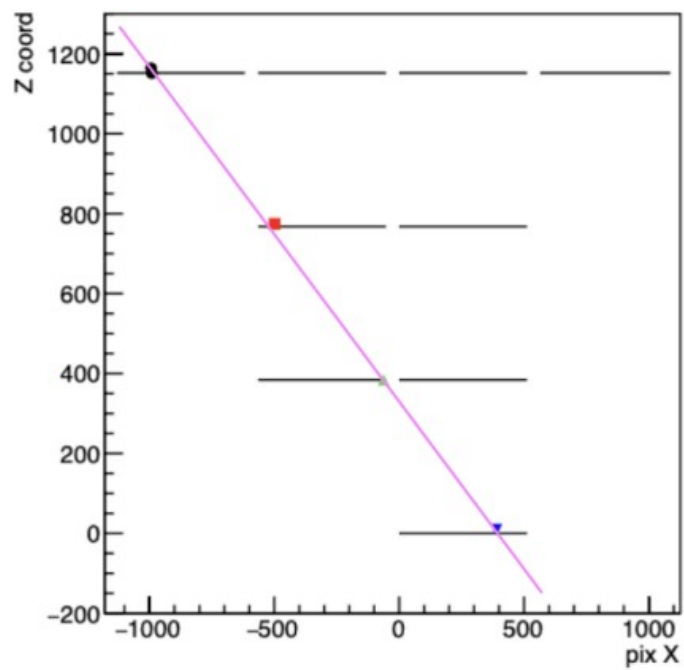


**Extra deep p-well (EDPW)**



**Gap in the n- layer (NGAP)**



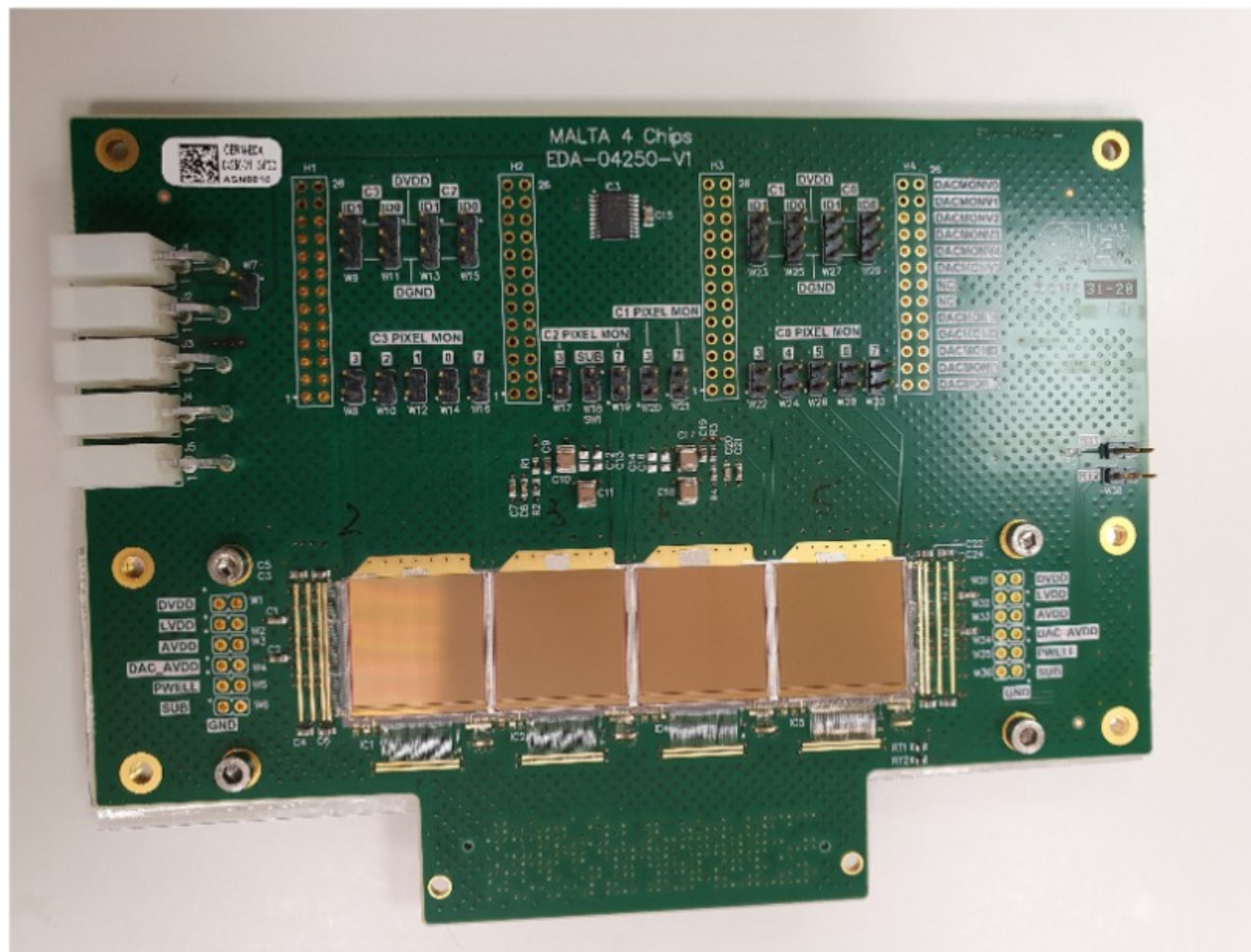


P0: Quad Chip

P1: Dual Chip

P2: Dual Chip

P3: Single chip



## Contact

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